Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	2	K/W
Thermal resistance, junction - ambient	R_{thJA}	Thermal resistance, junction- ambient, leaded	-	-	62	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
DC blocking voltage	V_{DC}	I_R=0.05 mA, T_j=25 °C	1200	-	-	V
Diode forward voltage	V_F	I_F=5 A, T_j=25 °C	-	1,65	1,8	
		I_F=5 A, T_j=150 °C	-	2,55	-	
Reverse current	I_R	V_R=1200 V, T_j=25 °C	-	5	120	µA
		V_R=1200 V, T_j=150 °C	-	20	1000	
AC characteristics						
Total capacitive charge	Q_c	V_R=400 V,$I_F \leq I_{F,max}$, di_F/dt=200 A/µs, T_j=150 °C	-	18	-	nC
Switching time[2)]	t_c		-	-	<10	ns
Total capacitance	C	V_R=1 V, f=1 MHz	-	250	-	pF
		V_R=300 V, f=1 MHz	-	20	-	
		V_R=600 V, f=1 MHz	-	18	-	

[1)] J-STD20 and JESD22

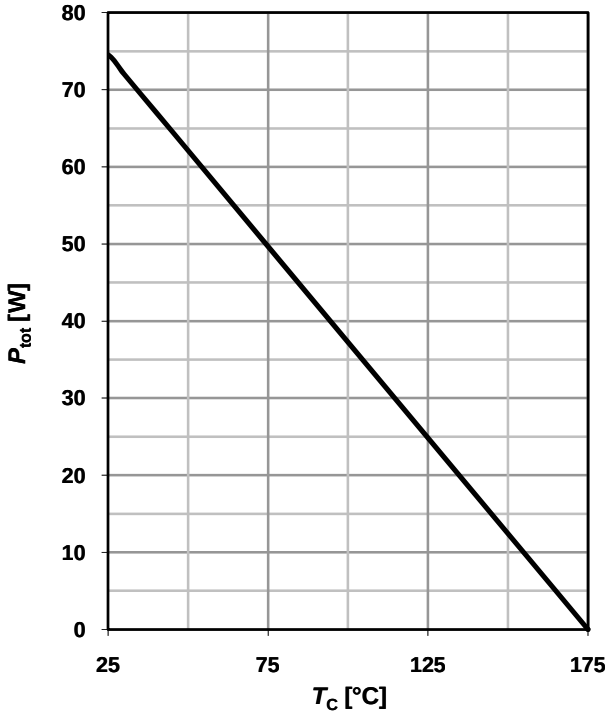
[2)] t_c is the time constant for the capacitive displacement current waveform (independent from T_j, I_{LOAD} and di/dt), different from t_{rr} which is dependent on T_j, I_{LOAD} and di/dt. No reverse recovery time constant t_{rr} due to absence of minority carrier injection

[3)] Under worst case Z_{th} conditions.

[4)] Only capacitive charge occuring, guaranteed by design

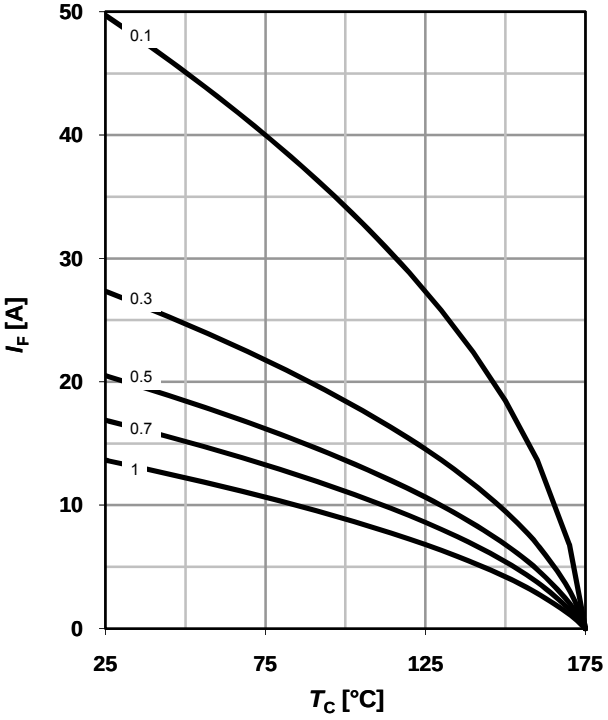
1 Power dissipation

$P_{tot}=f(T_C)$



2 Diode forward current

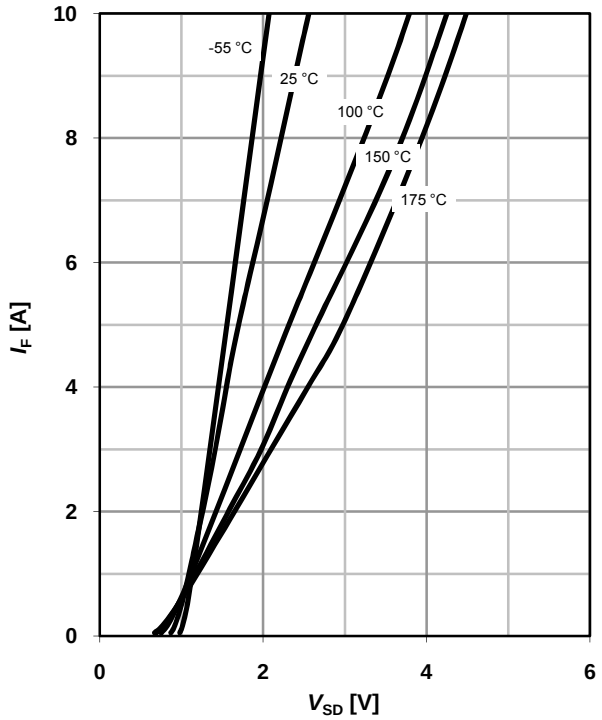
$I_F=f(T_C)^{3)}$; $T_j \leq 175$ °C; parameter: $D = t_p/T$



3 Typ. forward characteristic

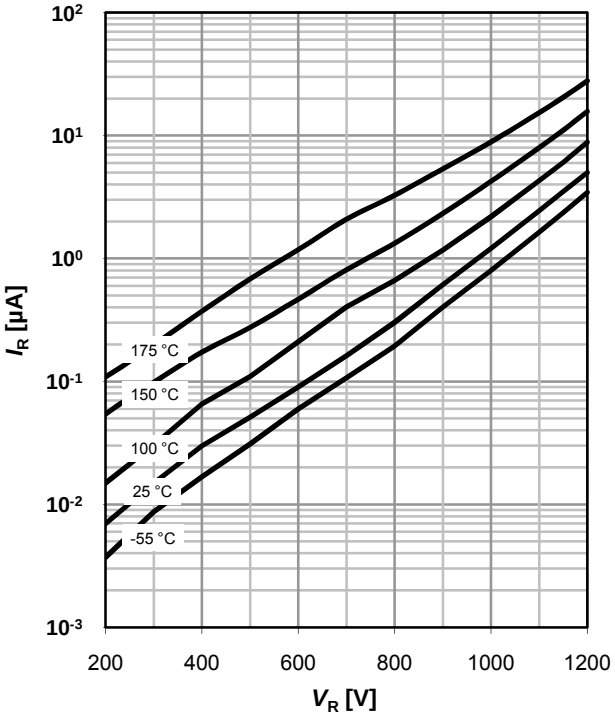
$I_F=f(V_F)$; $t_p=400$ µs

parameter: T_j



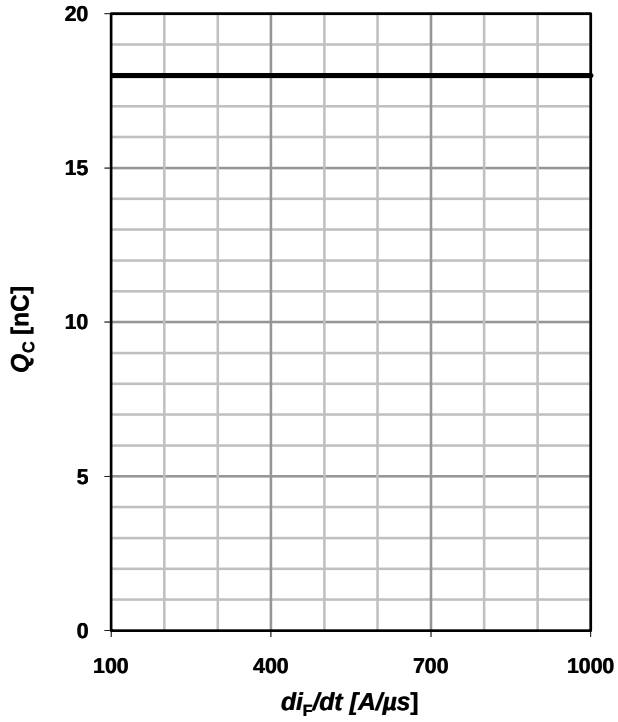
4 Typ. Reverse current vs. reverse voltage

$E_C=f(V_R)$



5 Typ. capacitance charge vs. current slope

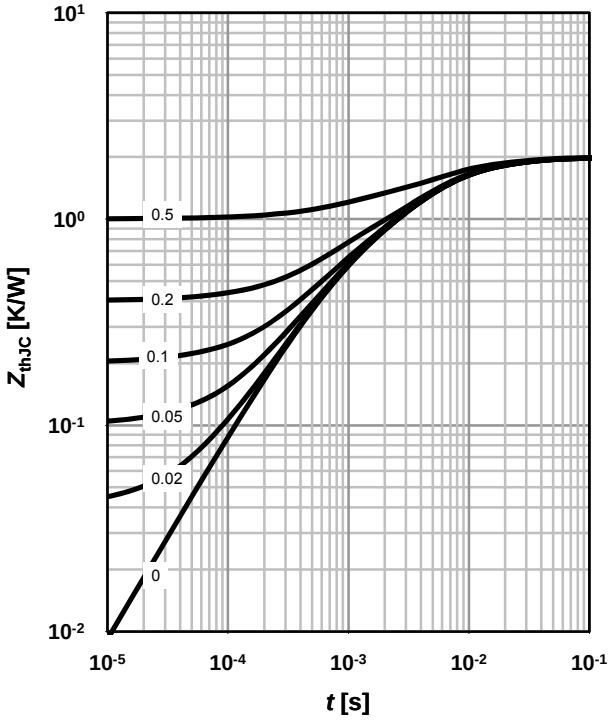
$Q_C=f(di_F/dt)$[4]; T_j=150 °C; $I_F \leq I_{F,max}$



6 Transient thermal impedance

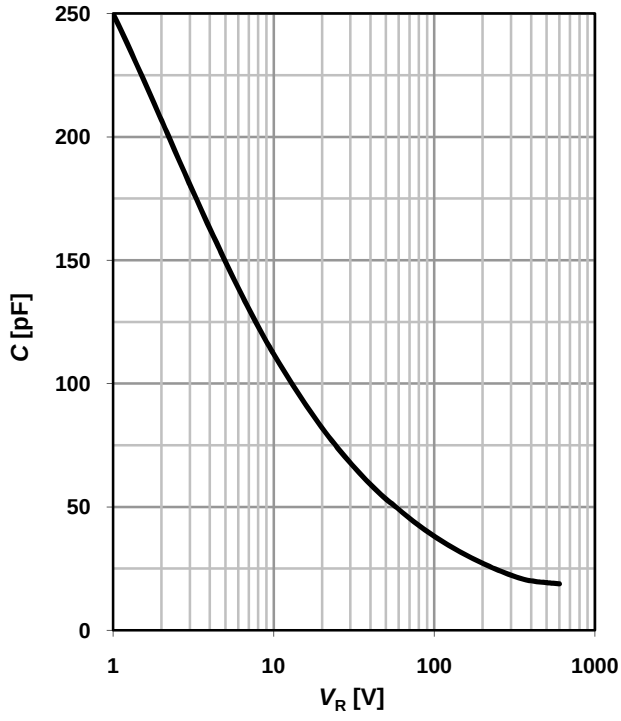
$Z_{thJC}=f(t_p)$

parameter: $D=t_p/T$



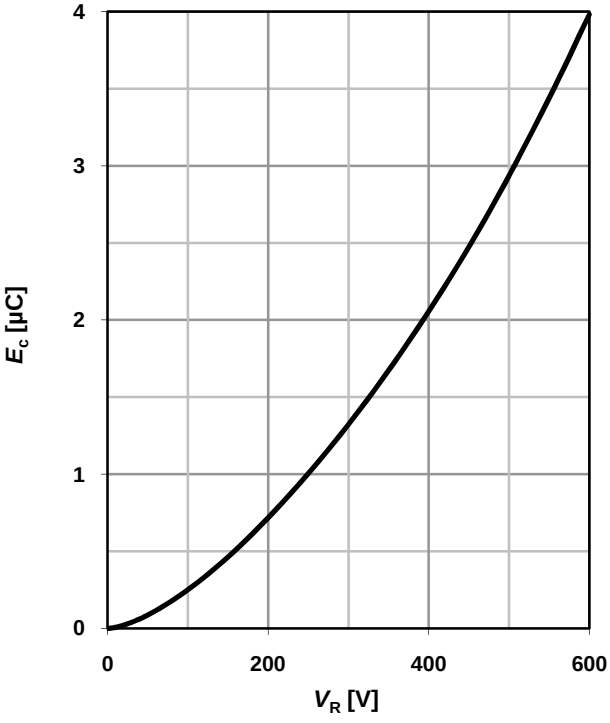
7 Typ. capacitance vs. reverse voltage

$C=f(V_R)$; T_C=25 °C, f=1 MHz

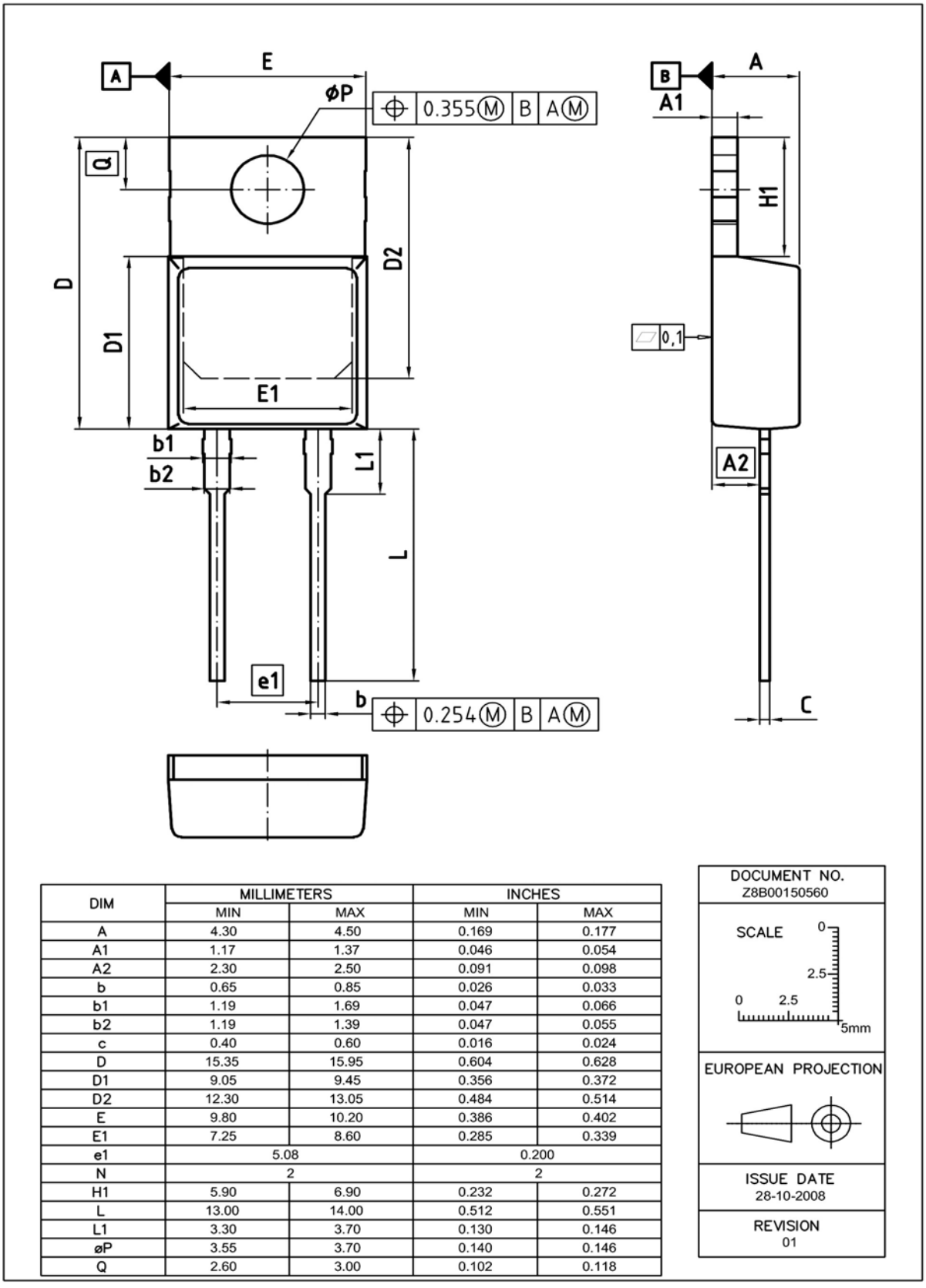


8 Typ. C stored energy

$E_C=f(V_R)$



PG-TO220-2: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.50	0.169	0.177
A1	1.17	1.37	0.046	0.054
A2	2.30	2.50	0.091	0.098
b	0.65	0.85	0.026	0.033
b1	1.19	1.69	0.047	0.066
b2	1.19	1.39	0.047	0.055
c	0.40	0.60	0.016	0.024
D	15.35	15.95	0.604	0.628
D1	9.05	9.45	0.356	0.372
D2	12.30	13.05	0.484	0.514
E	9.80	10.20	0.386	0.402
E1	7.25	8.60	0.285	0.339
e1	5.08		0.200	
N	2		2	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	3.30	3.70	0.130	0.146
øP	3.55	3.70	0.140	0.146
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00150560

SCALE 0 2.5 0 2.5 5mm

EUROPEAN PROJECTION

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REVISION
01

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